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(54) **SEMICONDUCTOR DEVICE**

(71) Applicant: **SK hynix Inc.**, Icheon (KR)

(72) Inventors: **Kyung Seop KIM**, Icheon (KR); **Chi Ho Kim**, Icheon (KR); **Young Cheol Song**, Icheon (KR); **Jae Wan Choi**, Icheon (KR)

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(57)

ABSTRACT

A semiconductor device is provided. The semiconductor device according to an implementation of the disclosed technology may include a variable resistance layer; a selector layer disposed over or under the variable resistance layer; a first protective layer disposed on sidewalls of the variable resistance layer and sidewalls of the selector layer, the first protective layer including silicon (Si) and nitrogen (N) and having a nitrogen (N) content higher than a silicon (Si) content; and a second protective layer disposed over the first protective layer, the second protective layer including silicon (Si) and nitrogen (N) and having a silicon (Si) content higher than a nitrogen (N) content.

